

N-channel LFPAK 100V 27.5 mΩ standard level MOSFET

Rev. 02 — 30 March 2010

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

#### 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

#### 1.4 Quick reference data

#### Table 1. Quick reference

- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package
- Motor control
- Server power supplies

Table 1.	QUICK reference					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	-	-	42	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	89	W
Tj	junction temperature		-55	-	175	°C
Avalance	he ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy		-	-	68	mJ
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A;	-	10.3	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 50 V$ ; see Figure 15 and <u>16</u>	-	33	-	nC

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Table 1.	Quick referencecontinued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cl	haracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; see <u>Figure 13</u>	-	-	52	mΩ
		$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 15 \text{ A}; \\ T_{j} = 25 \text{ °C}; \text{ see } \underline{\text{Figure } 14} \end{array}$	-	21.4	27.5	mΩ

### 2. Pinning information

Table 2.	Pinning	information				
Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	S	source		_		
2	S	source	mb			
3	S	source				
4	G	gate	q			
mb	D	mounting base; connected to drain	$\begin{array}{c} \hline 1 & 2 & 3 & 4 \end{array}$	mbb076 S		
			SOT669 (LFPAK)			

### 3. Ordering information

Table 3. Ordering information				
Type number Package				
	Name	Description	Version	
PSMN028-100YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669	

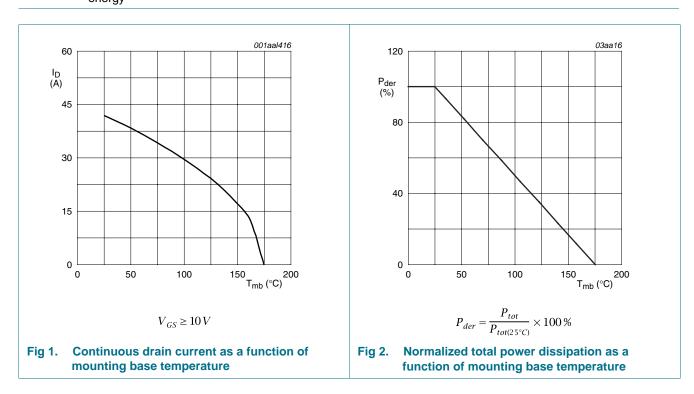
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### 4. Limiting values

#### Table 4. Limiting values

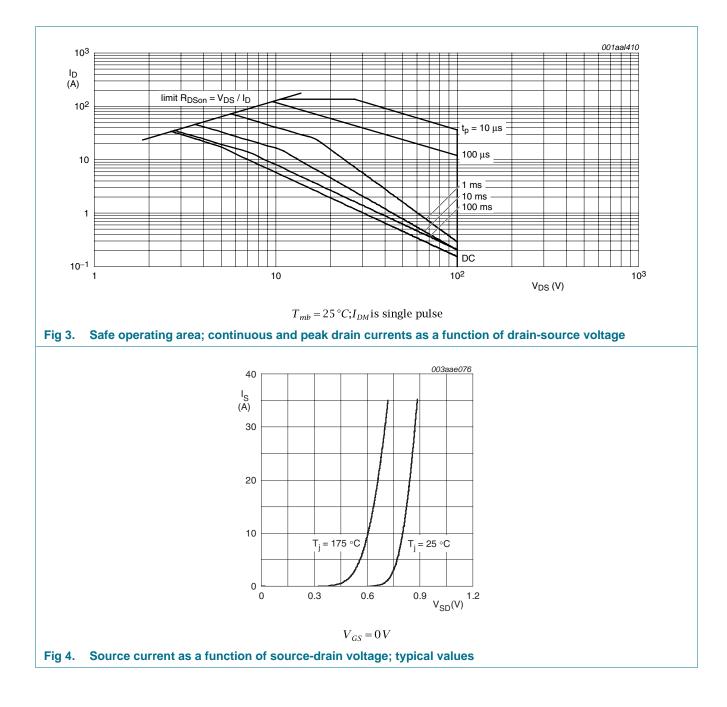
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Mire	Mox	l Init
Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
$V_{DGR}$	drain-gate voltage	T <sub>j</sub> ≤ 175 °C; T <sub>j</sub> ≥ 25 °C; R <sub>GS</sub> = 20 kΩ	-	100	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	-	30	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	-	42	А
I <sub>DM</sub>	peak drain current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	137	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	89	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-dra	ain diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C; see <u>Figure 4</u>	-	42	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	137	А
Avalanche	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 34 A; $V_{sup}$ ≤ 100 V; unclamped; $R_{GS}$ = 50 $\Omega$	-	68	mJ



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### 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see <u>Figure 5</u>	-	0.81	1.68	K/W
1					001aal406	
Z <sub>th(j-mb)</sub>	δ = 0.5					
(K/W)						

10<sup>-3</sup>

Fig 5. Transient termal impedance from junction to mounting base as a function of pulse duration

10<sup>-2</sup>

10<sup>-1</sup>

1

t<sub>p</sub> (s)

#### Table 5. Thermal characteristics

0.2

0.1

0.05

single shot

10<sup>-5</sup>

10<sup>-4</sup>

10-1

10<sup>-2</sup>

10<sup>-6</sup>

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### 6. Characteristics

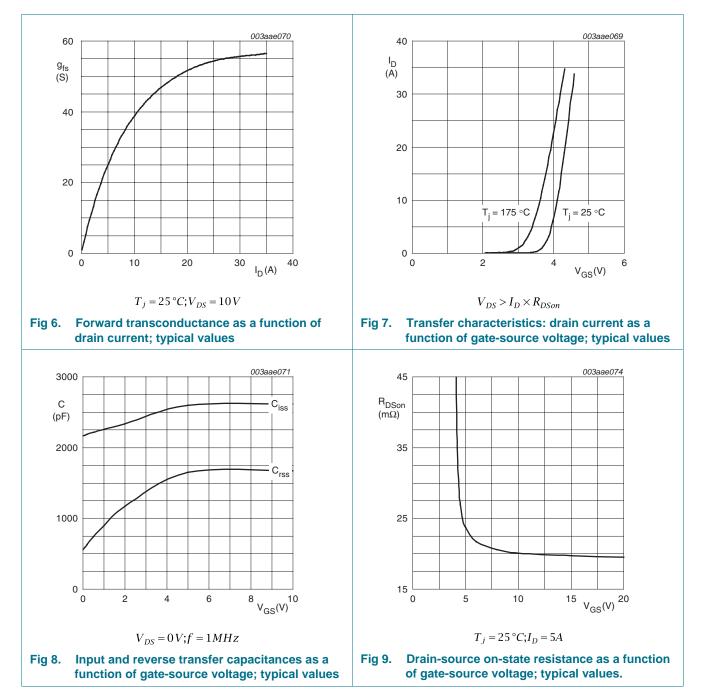
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	90	-	-	V
	breakdown voltage	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; see <u>Figure 11</u>	1	-	-	V
	voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; see Figure 12 and 11	2	3	4	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; see <u>Figure 11</u>	-	-	4.7	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 125 °C	-	-	50	μΑ
		$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.02	2	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see <u>Figure 13</u>	-	-	52	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; see <u>Figure 13</u>	-	49.9	74.3	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 25 °C; see <u>Figure 14</u>	-	21.4	27.5	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.5	1.5	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 15 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V; see Figure 15 and $\underline{16}$	-	33	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	25	-	nC
$Q_{GS}$	gate-source charge	$I_D$ = 15 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V; see Figure 15 and $\underline{16}$	-	7.2	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D$ = 15 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V; see <u>Figure 15</u>	-	5	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	2.2	-	nC
$Q_{GD}$	gate-drain charge	$I_D$ = 15 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V; see Figure 15 and $\underline{16}$	-	10.3	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$V_{DS} = 50 \text{ V}$ ; see <u>Figure 15</u> and <u>16</u>	-	4.1	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C;	-	1634	-	pF
C <sub>oss</sub>	output capacitance	see Figure 17	-	132	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	85	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 3.3 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	15	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \ \Omega; T_j = 25 \ ^{\circ}C$	-	14	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	33	-	ns
t <sub>f</sub>	fall time		-	12	-	ns

Source-drain diode

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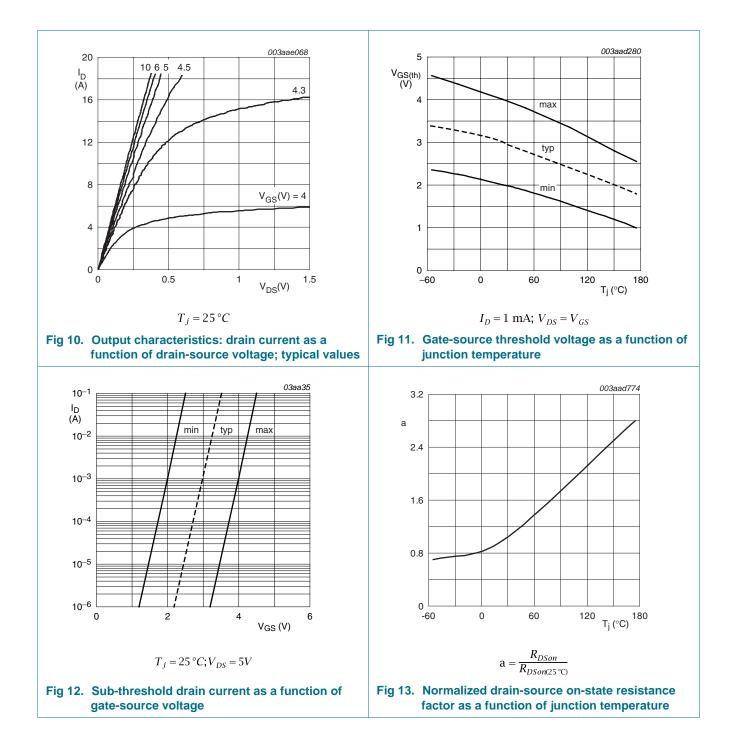
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Table 6.	Characteristics continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{SD}$	source-drain voltage	$I_S$ = 15 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C; see <u>Figure 4</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 5 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	48.7	-	ns
Qr	recovered charge	$V_{DS} = 50 V$	-	95.7	-	nC



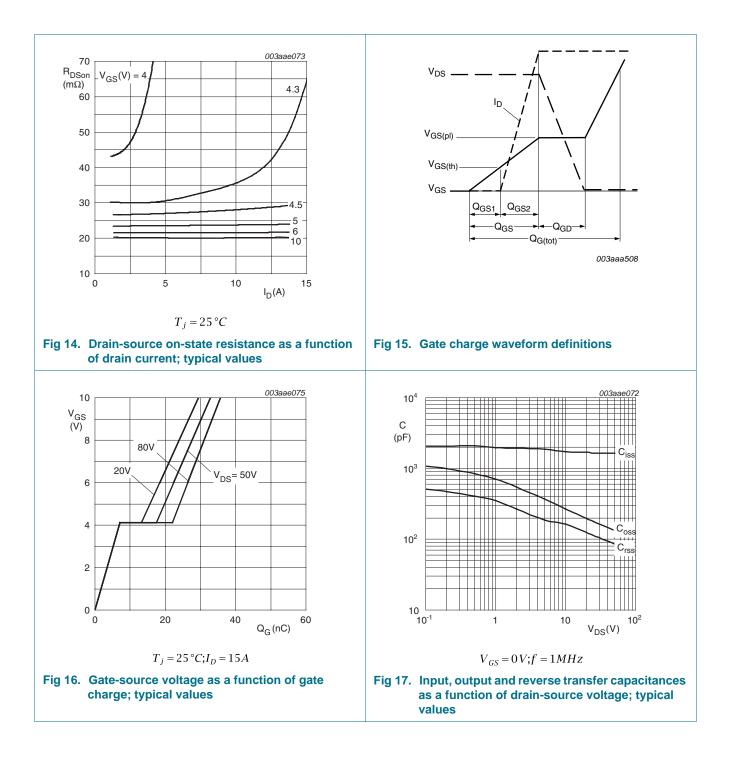
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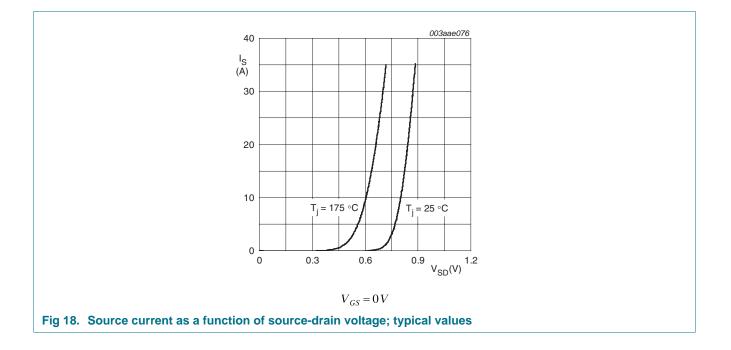
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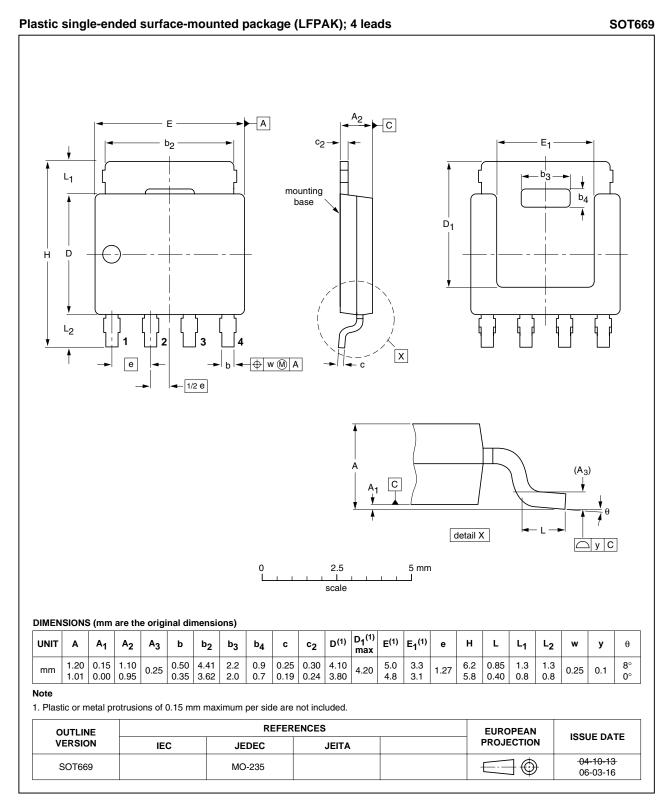
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### 7. Package outline



#### Fig 19. Package outline SOT669 (LFPAK)

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### 8. Revision history

Table 7. Revision his	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN028-100YS_2	20100330	Product data sheet	-	PSMN028-100YS_1
Modifications:	<ul> <li>Status chail</li> </ul>	nged from objective to pr	oduct.	
	<ul> <li>Various cha</li> </ul>	anges to content.		
PSMN028-100YS_1	20100210	Objective data sheet	-	-

### 9. Legal information

#### 9.1 Data sheet status

Document status [1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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